

L Number	Hits	Search Text	DB	Time stamp
1	2930000	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 15:59
2	28893	(memory or storage) and resistance with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:01
3	13957	(memory or storage) and resistive with (cell or element or unit)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:02
4	41173	((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:02
5	3181	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:10
6	833	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)) and (mram or magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:03
7	1301	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 with diode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:04
8	373	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)) and (mram or magnetic)) and 365/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:09
10	39	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and variable adj resistive) and select\$5 adj2 (transistor or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:17
9	162	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and variable adj resistive	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:14
11	3439	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and resist\$6 with diode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:17
12	1040	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and resist\$6 with diode) and cell with diode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:17
13	425	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and resist\$6 with diode) and cell with diode) and 365/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:18

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2	28893	(memory or storage) and resistance with cell	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:01
3	13957	(memory or storage) and resistive with (cell or element or unit)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:02
4	41173	((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:02
5	3181	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:10
6	833	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)) and (mram or magnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:03
7	1301	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 with diode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:04
8	373	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)) and (mram or magnetic)) and 365/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:09
9	162	((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and variable adj resistive	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:10
10	39	(((((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))) and variable adj resistive) and select\$5 adj2 (transistor or element)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/17 16:12